Epic TechWatch 2023



@ W3+ Fair Jena 30.11.2023

"Innovations in Ion Beam Machining"

Dr. Christian Schindler

Close to customers

Global network

2

Family owned

Innovation and education

O 12,700 FTE employees



CHF 3.0 bn

5% of turnover for innovation



BUHLER

Buhler Product Line Center of Competence Leipzig

Correcting, Structuring and Smoothing of Surfaces



Substrate Handling, Automation

Thin Film and Thickness Measurement etc.



Ion Beam Figuring (IBF). Corrective polishing of surfaces.

> Contactless and dry. Using accelerated argon ions.



Center of Competence Leipzig

Production Equipment for Correcting, Structuring and Smoothing of Surfaces

For precise figure correction and smoothing of high-end optics

For precise flattening and correction of features on a wafer





Leybold Optics IBF - Series

Leybold Optics IBT800



Applications of Ion Beam Figuring (IBF) Ultraprecision as standard





Leybold Optics IBF.

Machine Portfolio (Number of Axes: 3, 5 or 6).

Model	IBF 200	IBF 450	IBF 600	IBF 800	IBF 1200	IBF 1500	IBF 2100
Max. diameter of flat samples	200 mm	500 mm	600 mm	800 mm	1200 mm	1500 mm	2100 mm
Max. weight	35 kg	100 kg	100 kg	100 kg	300 kg	1000 kg	1500 kg



1631





Leybold Optics IBF Reproducible and Longterm Stable IB-Sources for Material Removal

RF40 ion beam source







1,8 nm/s	Peak Etch Rate	30 nm/s	
9 mm	Spot Size (FWHM)	17.5 mm	
0,01mm ³ /min	Removal Rate	0.63 mm³/min	

RF80 ion beam source

Scan 9

-10

[mm]

-20

1 X Measured Data

1 Y Measured Data

1 X Calculated Data — 1 X Threshold
1 Y Calculated Data — 1 Y Threshold
X Threshold

20

10







10

Etch rate measurement

Initial situation

- Every ion beam source has its own characteristic and working point
- Individual beam center and etch rate needs to be determined

Standard measurement is done via 2 steps

- 1. Measure beam current over beam profile with faraday cup and extract a graph to obtain gaussian shape and beam center (only indirect, uncertian etch rate determination)
- 2. Perform a footprint or groove etching on sample to analyse etch rate outside of machine
- → High effort to obtain actual etch rate and monitor longterm degeneration of source (drift sums up to ~10% after 500h)

ISERM

- Direct determine etch rate with actual beam parameter and material in the machine
- → Enable regular process calibration and secure production yield by stable material removal and predictive maintanance
- \rightarrow Obtain basis for process simulation



RF power: < 300 W Ion energy: < 1500 eV Ion current: < 150 mA Accelerator voltage: < 1000 V







In-Situ Etch Rate Measurement System - ISERM





Automation Solutions for IBF

Robotic handling

- Combined loading of several IBF machines within robotic cell on rails
- ➢ work stocker arrangement
- > 24/7 operation mode
- Flexible actuator design

Array machining

- Take advantage of larger equipment for small samples to increase efficiency
- Full software support for metrology and operations
- Quick setup and low offset time









Innovations for a **better world.**

